CNA1014H (ON1387)

Photo Interrupter

For contactless SW, object detection

Overview

CNA1014H is a transmittive photosensor series in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

■ Features

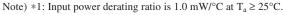
• Highly precise position detection: 0.3 mm

• With attachment positioning boss

• Fast response: t_r , $t_f = 5 \mu s$ (typ.)

■ Adsolute Maximum Ratings $T_a = 25$ °C

!	Symbol	Rating	Unit	
Input (Light	Reverse voltage	V_R	3	V
emitting diode)	Forward current	I_F	50	mA
	Power dissipation *1	P_{D}	75	mW
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	30	V
,	Emitter-collector voltage (Base open)	V _{ECO}	5	V
	Collector current	I_{C}	20	mA
	Collector power dissipation *2	P _C	100	mW
Temperature	Operating ambient temperature	T_{opr}	-25 to +85	°C
	Storage temperature	T _{stg}	-40 to +100	°C



^{*2:} Output power derating ratio is 1.33 mW/°C at $T_a \ge 25$ °C.

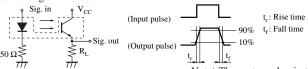
■ Electrical-Optical Characteristics $T_a = 25$ °C ± 3 °C

	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V_F	$I_F = 20 \text{ mA}$		1.25	1.40	V
characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
Output	Collector-emitter cutoff current	I _{CEO}	$V_{CE} = 10 \text{ V}$		10	200	nA
characteristics	(Base open)						
Transfer	Collector current	I_C	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}$	1.5		12.0	mA
characteristics	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 40 \text{ mA}, I_C = 1 \text{ mA}$			0.4	V
	Rise time *	t _r	$V_{CC} = 5 \text{ V}, I_C = 1 \text{ mA}$		5		μs
	Fall time *	$t_{\rm f}$	$R_L = 100 \Omega$		5		μs

Note) 1. Input and output are practiced by electricity.

2. This device is designed be disregarded radiation.

3. *: Switching time measurement circuit



Note) The part number in the parenthesis shows conventional part number.

Unit: mm

12.0

3.0±0.1

Center

12.0

3.0±0.1

Center

1.23

4-0.45±0.15

1.23

4-0.45±0.15

2. Cathode

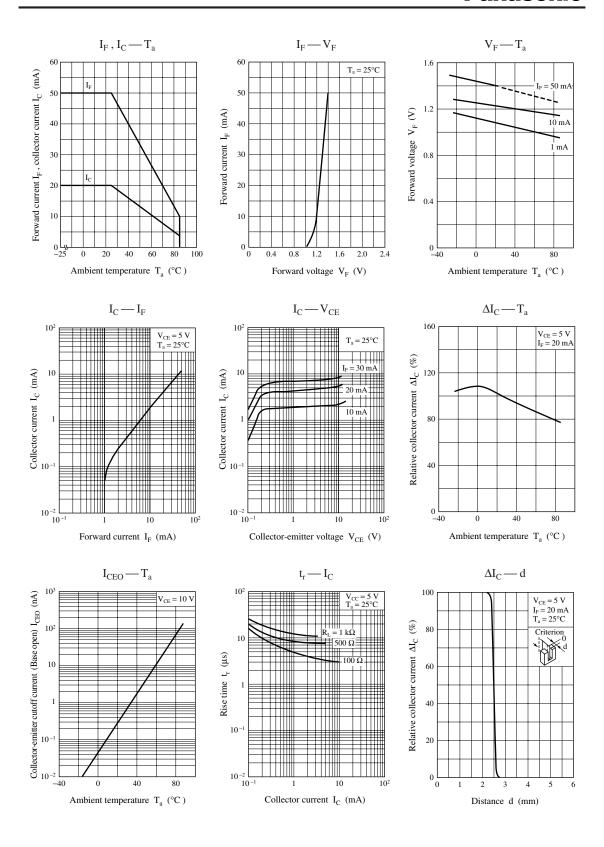
3: Collector

4: Emitter

PISTR104-025 Package

(Note) 1. Tolerance unless otherwise specified is ±0.3

2. () Dimension is reference



Caution for Safety

⚠ DANGER

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

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